

Product Summary

BV _{DSS}	R _{DS(ON)}	Package	I _D T _C = +25°C
800V	2.0Ω@V _{GS} = 10V	ITO220AB (Type TH)	7A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

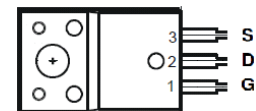
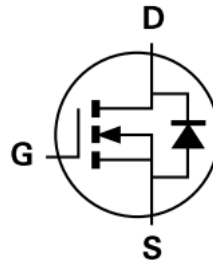
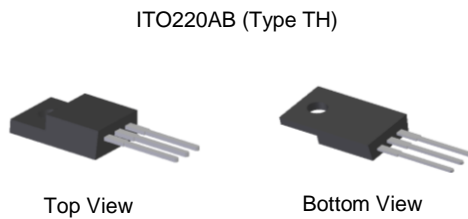
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: ITO220AB (Type TH)
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

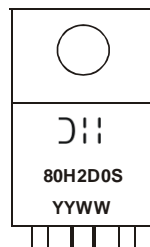


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN80H2D0SCT1	ITO220AB (Type TH)	50 pieces/tube

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



- ⌋⌋⌋ = Manufacturer's Marking
 80H2D0S = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Last Two Digits of Year (ex: 17 = 2017)
 WW or WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	800	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Continuous Drain Current (Note 9), V _{GS} = 10V	I _D	Steady State T _C = +25°C	7	A
		T _C = +100°C	4	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 9)	I _{DM}	28	A	
Avalanche Current (Note 6)	I _{AS}	2.0	A	
Avalanche Energy (Note 6)	E _{AS}	60	mJ	
Peak Diode Recovery dv/dt (Note 7)	dv/dt	2.8	V/ns	

Thermal Characteristics

Characteristic	Symbol	Max	Unit	
Power Dissipation (Note 5)	P _D	T _C = +25°C	41	W
		T _C = +100°C	16	
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	49.5	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	3	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	800	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	25	µA	V _{DS} = 800V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±30V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2.0	3.3	4.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	2.0	Ω	V _{GS} = 10V, I _D = 2.5A
Diode Forward Voltage	V _{SD}	—	0.86	1.5	V	V _{GS} = 0V, I _S = 7.0A
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iSS}	—	1253	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	115	—		
Reverse Transfer Capacitance	C _{rSS}	—	11	—		
Gate Resistance	R _g	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	35.4	—	nC	V _{GS} = 10V, V _{DS} = 560V, I _D = 7A
Gate-Source Charge	Q _{gs}	—	5.9	—		
Gate-Drain Charge	Q _{gd}	—	16.4	—		
Turn-On Delay Time	t _{D(ON)}	—	20.5	—	ns	V _{GS} = 10V, V _{DD} = 350V, R _G = 25Ω, I _D = 7A
Turn-On Rise Time	t _F	—	35.8	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	104	—	ns	
Turn-Off Fall Time	t _F	—	42.6	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	419	—	ns	di/dt = 100A/µs, V _{GS} = 0V, I _F = 7A
Body Diode Reverse Recovery Charge	Q _{RR}	—	4324	—	µC	

- Notes:
- Device mounted on an infinite heatsink.
 - Guaranteed by design. Not subject to production testing.
 - I_{SD} ≤ 4.5A, di/dt ≤ 200A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Drain current limited by maximum junction temperature.

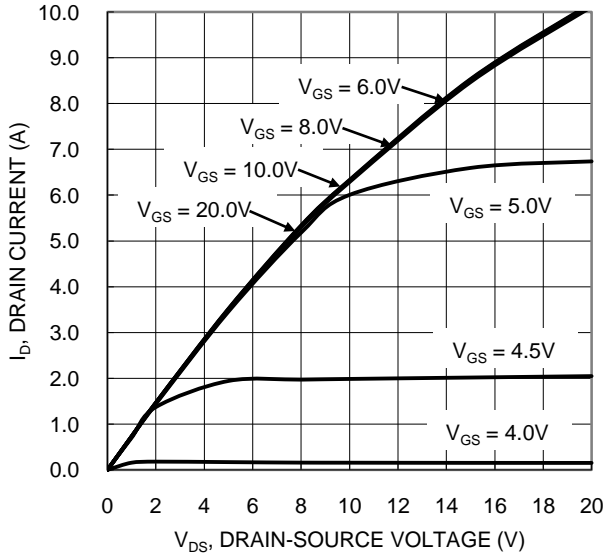


Figure 1. Typical Output Characteristic

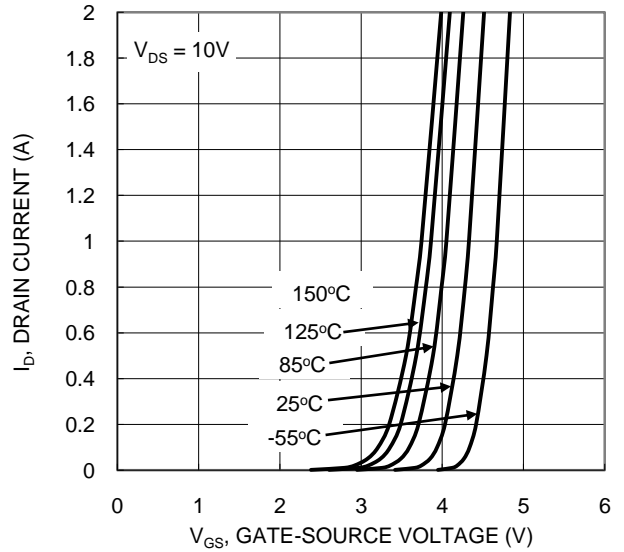


Figure 2. Typical Transfer Characteristic

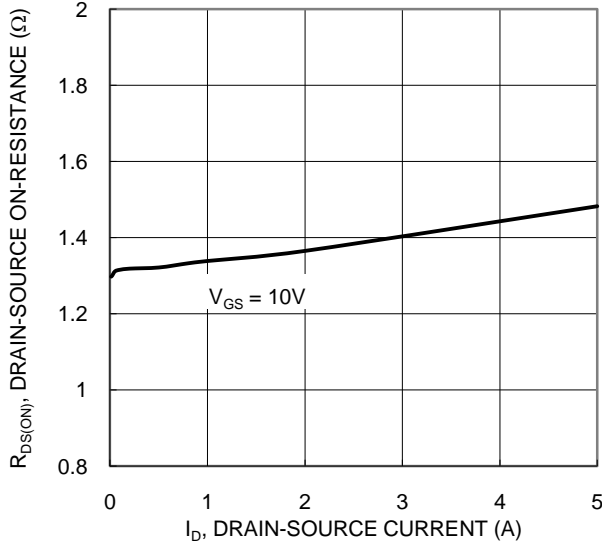


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

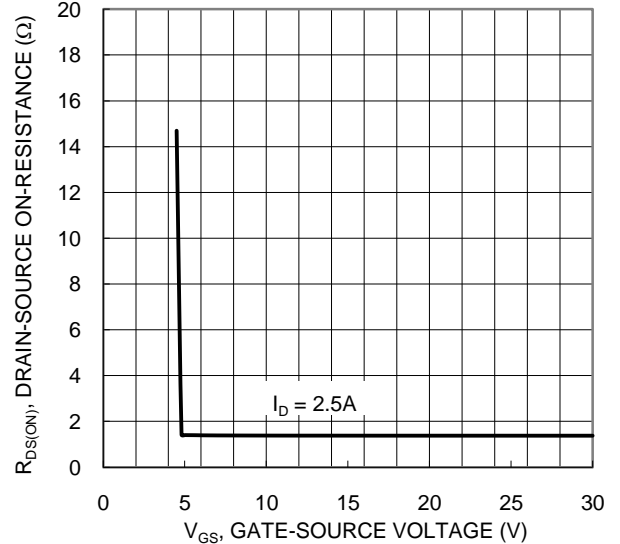


Figure 4. Typical Transfer Characteristic

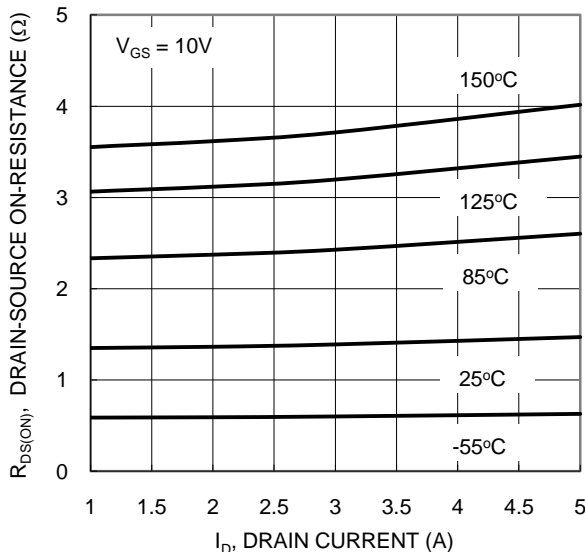


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

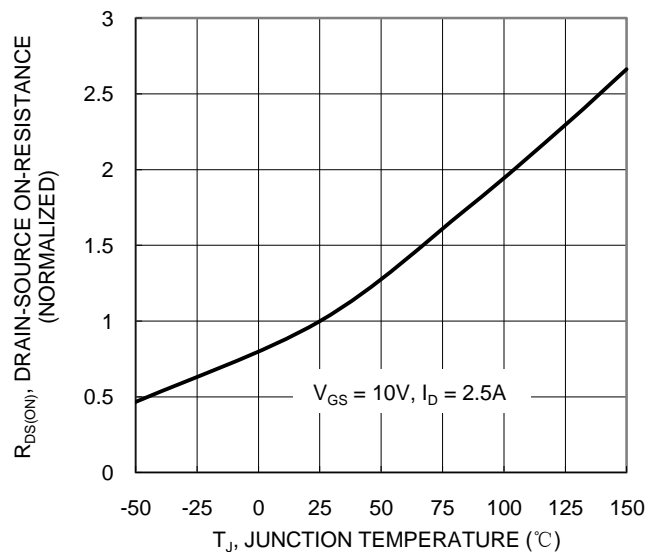


Figure 6. On-Resistance Variation with Temperature

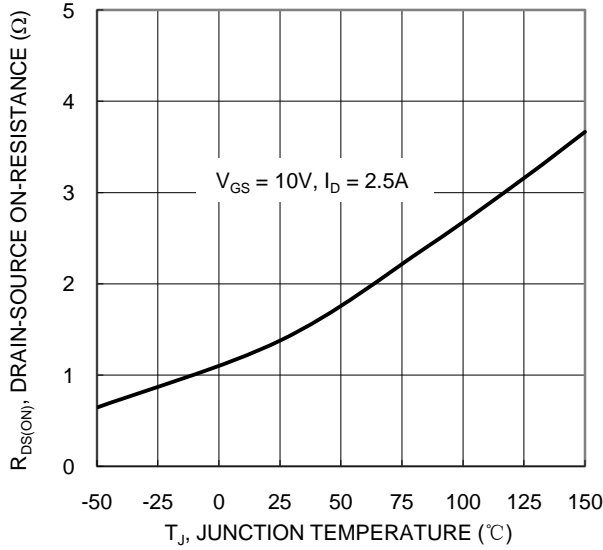


Figure 7. On-Resistance Variation with Temperature

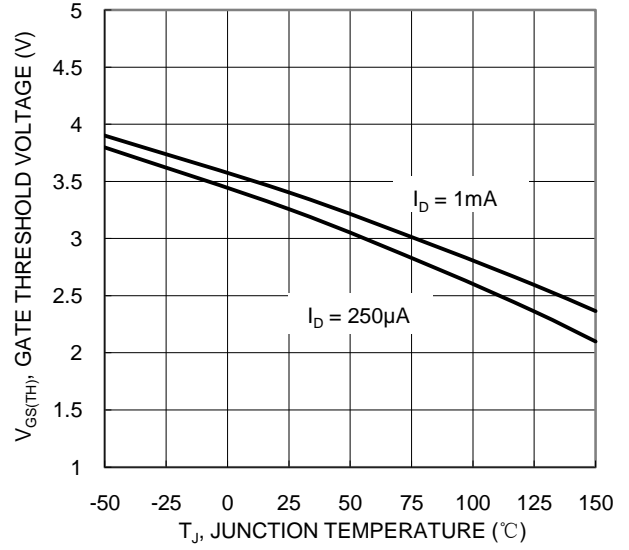


Figure 8. Gate Threshold Variation vs. Junction Temperature

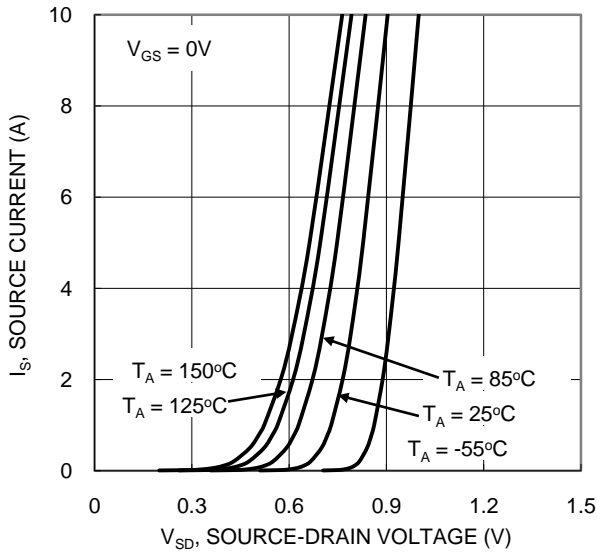


Figure 9. Diode Forward Voltage vs. Current

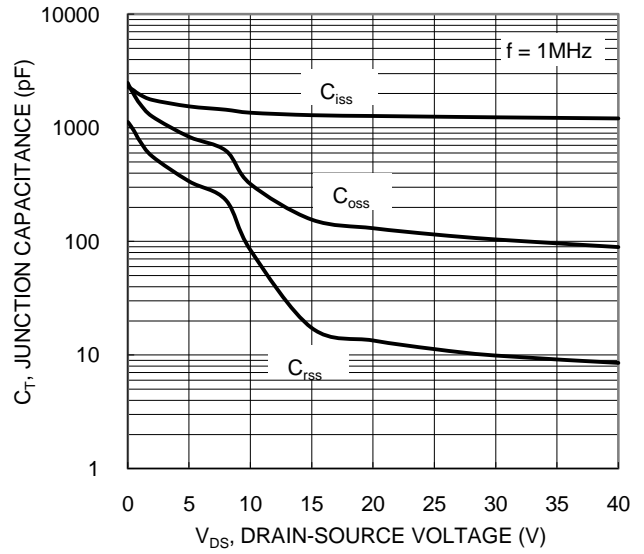


Figure 10. Typical Junction Capacitance

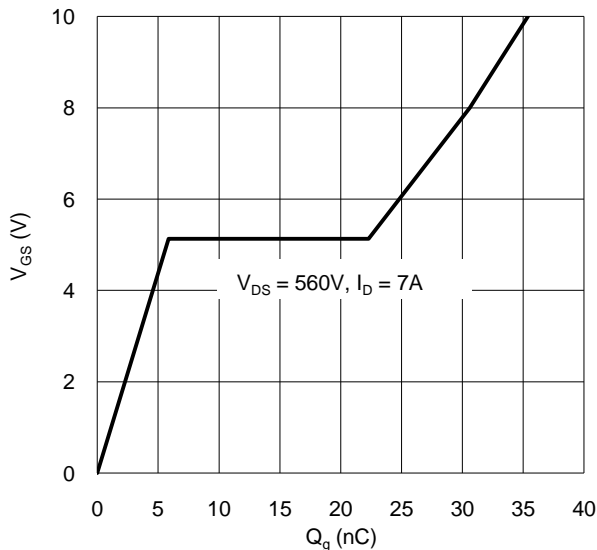


Figure 11. Gate Charge

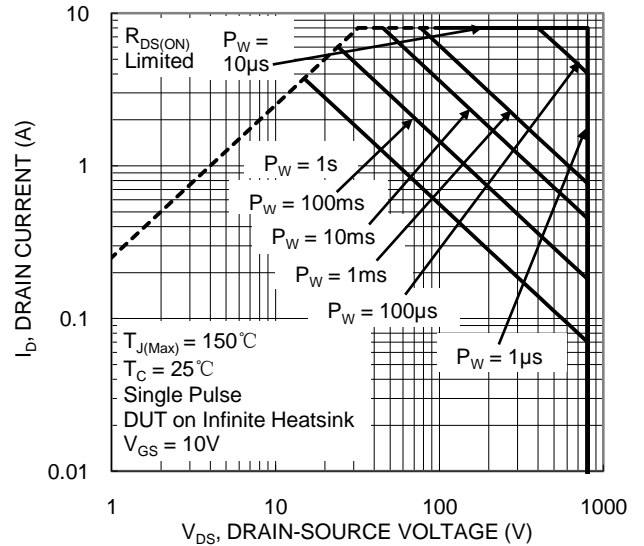


Figure 12. SOA, Safe Operation Area

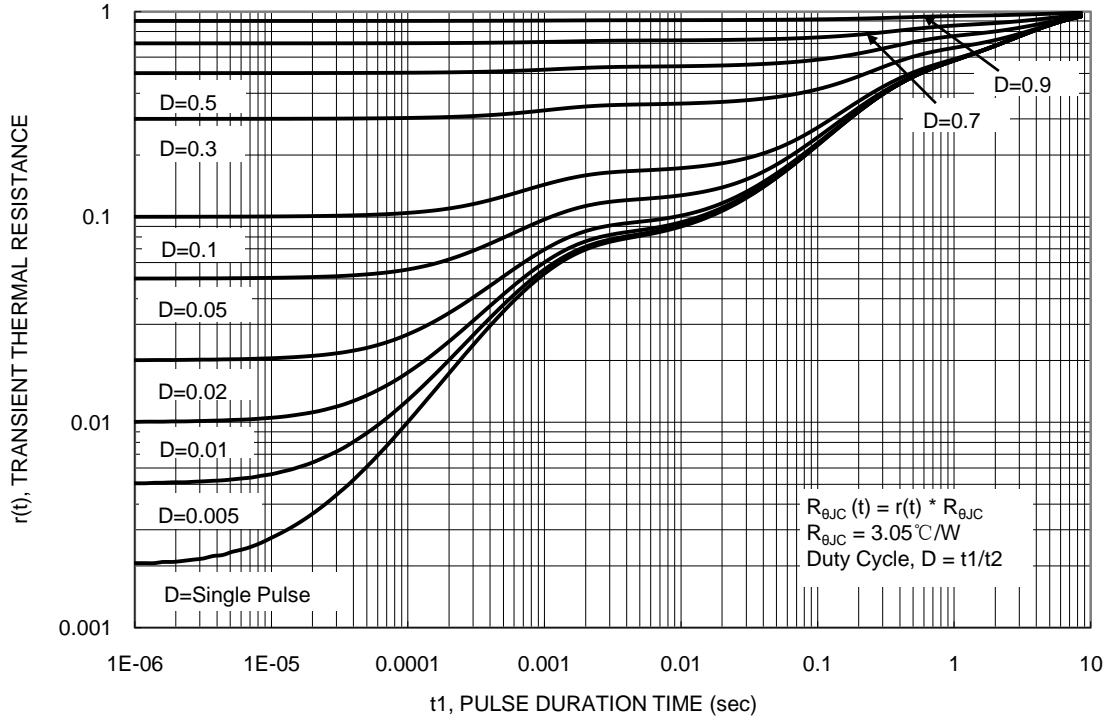
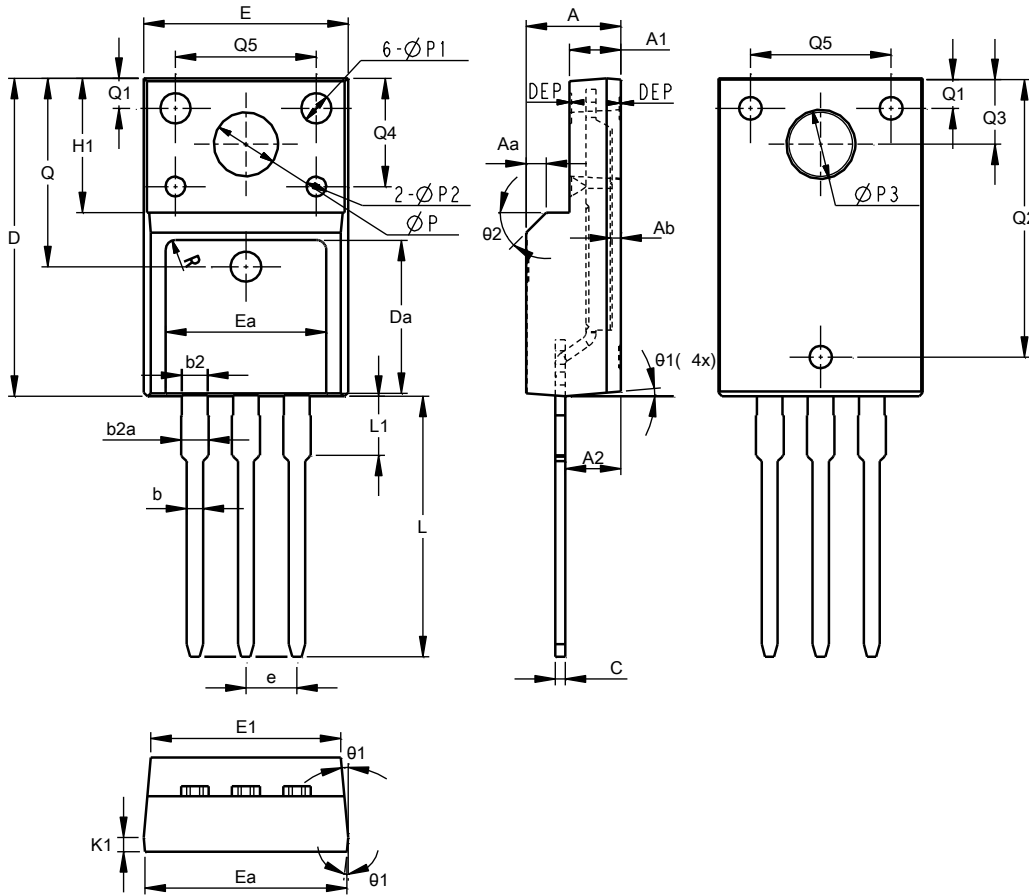


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

ITO220AB (Type TH)



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Dim	Min	Max	Typ
A	4.50	4.90	4.70
A1	2.34	2.74	2.54
A2	2.63	2.89	2.76
Aa	1.00 REF		
Ab	0.30	0.60	0.56
b	0.75	0.90	0.80
b2	1.23	1.38	1.28
b2a	1.25	1.45	1.35
c	0.45	0.60	0.50
D	15.47	16.27	15.87
Da	7.55	8.05	7.80
e	2.54 BSC		
E	9.86	10.46	10.16
E1	9.26	9.66	9.46
Ea	7.70	8.30	8.00
Eb	9.76	10.34	10.04
H1	6.70 REF		
L	12.58	13.38	12.98
L1	2.81	3.05	2.93
K1	0.65	0.75	0.70
Q	9.40 REF		
Q1	1.00	2.00	1.50
Q2	13.50	14.30	13.90
Q3	3.15	3.45	3.30
Q4	5.15	5.65	5.40
Q5	6.70	7.30	7.00
ØP	3.06	3.40	3.18
ØP1	1.40	1.60	1.50
ØP2	0.95	1.05	1.00
ØP3	3.30	3.60	3.45
θ1	3°	7°	5°
θ2	-	45°	-
R	0.50 REF		
DEP	0.05	0.15	0.10
All Dimensions in mm			

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